

Chip Specification

General Description:

Schottky Diode chips with Mo-barrier for switch mode power rectifiers with the following features:

- * **Guard-ring for stress protection**
- * **Extremely low forward voltage**
- * **125 °C operation junction temperature**
- * **reverse avalanche behavior**

Mechanical Data:

MBR1025passivated Silicon Chip

Dimension(mil):	108x128 mil
Thickness:	350 +- 20 µm
Metallization:	
Top (Anode) :	Al (AlAg)*
Bottom (Cathode) :	TiNiAg



Forward Current (A):	10A
Reverse Voltage (V):	>27V

Type	Chip size(mil)	V _F (V)@25 C at I _f =10A	V _F (V)@25 C at I _f =20A	I _{RM} @V _{RMM} at 25 C
MBR1025	108x128	<0,4V	<0,5V	0,6mA

* Available in both variants

expected value for recommended assembling with both side soldering

Typical device : PBYL1025, 19TQ015

